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FORM PTO-1449 (Equivalent)

U.S. Department of Commerce Patent and Trademark Office

U.S. Application Serial No. 09/506,425

Atty. Docket No.
AM-3751

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Sara Giordani Applicants

Аррисация

February 17, 2000 Filing Date

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(Use several sheets if necessary)

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Examiner Initial	Document Number	Issue Date	Name	Class	Subclass	Filing Date If Appropriate
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ofero.	EP 0565212	Europe	10/13/93	Wong et al.	H01L	21/306	
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Alla a. Ohe 1/26/02

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

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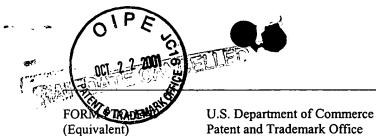
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<u>Initial</u>	Number	<u>Date</u>	Name	<u>Class</u>	Subclass	If Appropriate

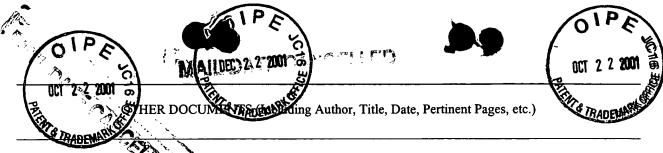
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